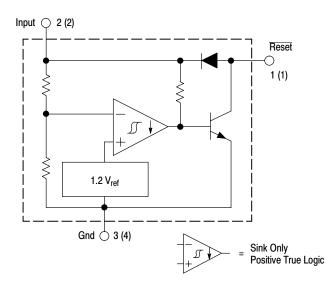
Micropower Undervoltage Sensing Circuits

The MC34164 series are undervoltage sensing circuits specifically designed for use as reset controllers in portable microprocessor based systems where extended battery life is required. These devices offer the designer an economical solution for low voltage detection with a single external resistor. The MC34164 series features a bandgap reference, a comparator with precise thresholds and built–in hysteresis to prevent erratic reset operation, an open collector reset output capable of sinking in excess of 6.0 mA, and guaranteed operation down to 1.0 V input with extremely low standby current. The MC devices are packaged in 3–pin TO–226AA, 8–pin SO–8 and Micro8 surface mount packages. The NCV device is packaged in SO–8.

Applications include direct monitoring of the 3.0 or 5.0 V MPU/logic power supply used in appliance, automotive, consumer, and industrial equipment.

- Temperature Compensated Reference
- Monitors 3.0 V (MC34164–3) or 5.0 V (MC34164–5) Power Supplies
- Precise Comparator Thresholds Guaranteed Over Temperature
- Comparator Hysteresis Prevents Erratic Reset
- Reset Output Capable of Sinking in Excess of 6.0 mA
- Internal Clamp Diode for Discharging Delay Capacitor
- Guaranteed Reset Operation With 1.0 V Input
- Extremely Low Standby Current: As Low as 9.0 μA
- Economical TO-226AA, SO-8 and Micro8 Surface Mount Packages



Pin numbers adjacent to terminals are for the 3–pin TO–226AA package. Pin numbers in parenthesis are for the 8–lead packages.

This device contains 28 active transistors.

Figure 1. Representative Block Diagram



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TO-226AA P SUFFIX CASE 29

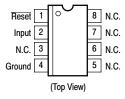


SO-8 D SUFFIX CASE 751



Micro8 DM SUFFIX CASE 846A

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 7 of this data sheet.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Power Input Supply Voltage	V _{in}	-1.0 to 12	V
Reset Output Voltage	Vo	-1.0 to 12	V
Reset Output Sink Current	I _{Sink}	Internally Limited	mA
Clamp Diode Forward Current, Pin 1 to 2 (Note 1)	I _F	100	mA
Power Dissipation and Thermal Characteristics P Suffix, Plastic Package Maximum Power Dissipation @ T _A = 25°C Thermal Resistance, Junction–to–Air D Suffix, Plastic Package Maximum Power Dissipation @ T _A = 25°C Thermal Resistance, Junction–to–Air DM Suffix, Plastic Package Maximum Power Dissipation @ T _A = 25°C Thermal Resistance, Junction–to–Air	P _D R _{θJA} P _D R _{θJA} P _D R _{θJA}	700 178 700 178 520 240	mW °C/W mW °C/W mW °C/W
Operating Junction Temperature	T _J	+150	°C
Operating Ambient Temperature Range MC34164 Series MC33164 Series, NCV33164	T _A	0 to +70 - 40 to +125	°C
Storage Temperature Range	T _{stg}	- 65 to +150	°C

NOTE: ESD data available upon request.

MC34164-3, MC33164-3 SERIES

ELECTRICAL CHARACTERISTICS (For typical values $T_A = 25$ °C, for min/max values T_A is the operating ambient temperature range that applies [Notes 2 & 3], unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
COMPARATOR					
Threshold Voltage High State Output (V_{in} Increasing) Low State Output (V_{in} Decreasing) Hysteresis (I_{Sink} = 100 μ A)	V _{IH} V _{IL} V _H	2.55 2.55 0.03	2.71 2.65 0.06	2.80 2.80 –	V
RESET OUTPUT					
Output Sink Saturation $ (V_{in} = 2.4 \text{ V}, I_{Sink} = 1.0 \text{ mA}) $ $ (V_{in} = 1.0 \text{ V}, I_{Sink} = 0.25 \text{ mA}) $	V _{OL}	- -	0.14 0.1	0.4 0.3	V
Output Sink Current (V _{in} , Reset = 2.4 V)	I _{Sink}	6.0	12	30	mA
Output Off-State Leakage (V _{in} , Reset = 3.0 V) (V _{in} , Reset = 10 V)	^l R(leak)	- -	0.02 0.02	0.5 1.0	μΑ
Clamp Diode Forward Voltage, Pin 1 to 2 (I _F = 5.0 mA)	V _F	0.6	0.9	1.2	٧
TOTAL DEVICE					
Operating Input Voltage Range	V _{in}	1.0 to 10	-	_	V
Quiescent Input Current $V_{in} = 3.0 \text{ V}$ $V_{in} = 6.0 \text{ V}$	l _{in}	_ _	9.0 24	15 40	μΑ

Maximum package power dissipation limits must be observed.
 Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient as possible.
 T_{low} = 0°C for MC34164 Thigh = +70°C for MC34164 = +125°C for MC33164

MC34164-5, MC33164-5 SERIES, NCV33164-5

ELECTRICAL CHARACTERISTICS (For typical values $T_A = 25^{\circ}C$, for min/max values T_A is the operating ambient temperature range that applies [Notes 5 & 6], unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
COMPARATOR	<u>.</u>				•
Threshold Voltage					V
High State Output (V _{in} Increasing)	V_{IH}	4.15	4.33	4.45	
Low State Output (V _{in} Decreasing)	V_{IL}	4.15	4.27	4.45	
Hysteresis (I _{Sink} = 100 μA)	V_{H}	0.02	0.09	_	
RESET OUTPUT					
Output Sink Saturation	V _{OL}				V
$(V_{in} = 4.0 \text{ V}, I_{Sink} = 1.0 \text{ mA})$		_	0.14	0.4	
$(V_{in} = 1.0 \text{ V}, I_{Sink} = 0.25 \text{ mA})$		_	0.1	0.3	
Output Sink Current (V _{in} , Reset = 4.0 V)	I _{Sink}	7.0	20	50	mA
Output Off-State Leakage	^I R(leak)				μА
$(V_{in}, \overline{Reset} = 5.0 \text{ V})$, ,	_	0.02	0.5	
$(V_{in}, \overline{Reset} = 10 V)$		_	0.02	2.0	
Clamp Diode Forward Voltage, Pin 1 to 2 (I _F = 5.0 mA)	V _F	0.6	0.9	1.2	V
TOTAL DEVICE					
Operating Input Voltage Range	V _{in}	1.0 to 10	-	_	V
Quiescent Input Current	I _{in}				μΑ
$V_{in} = 5.0 \text{ V}$	""	_	12	20	
V_{in} = 10 V		_	32	50	

^{4.} Maximum package power dissipation limits must be observed.

 $T_{high} = +70^{\circ}C$ for MC34164

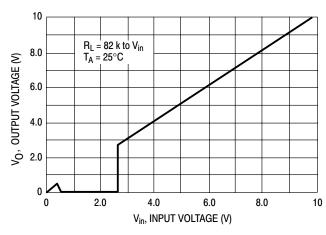


Figure 1. MC3X164–3 Reset Output Voltage versus Input Voltage

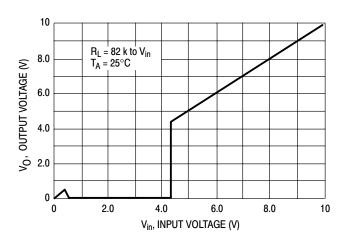


Figure 2. MC3X164-5 Reset Output Voltage versus Input Voltage

^{5.} Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient as possible.

^{6.} $T_{low} = 0^{\circ}C$ for MC34164 = $-40^{\circ}C$ for MC33164, NCV33164

⁼ -40° C for MC33164, NCV33164 = $+125^{\circ}$ C for MC33164, NCV33164 7. NCV prefix is for automotive and other applications requiring site and change control.

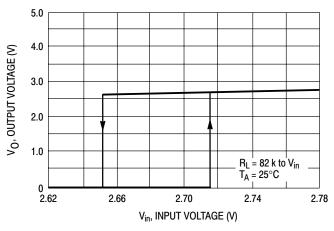


Figure 3. MC3X164-3 Reset Output Voltage versus Input Voltage

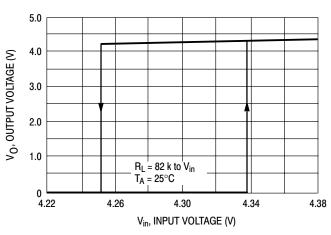


Figure 4. MC3X164-5 Reset Output Voltage versus Input Voltage

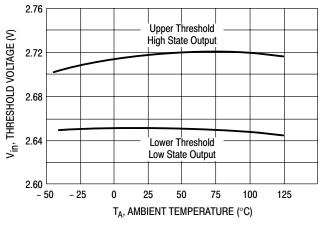


Figure 5. MC3X164–3 Comparator Threshold Voltage versus Temperature

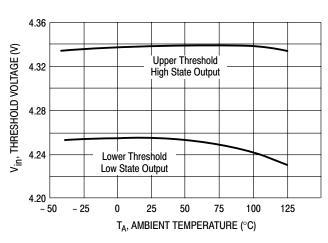


Figure 6. MC3X164–5 Comparator Threshold Voltage versus Temperature

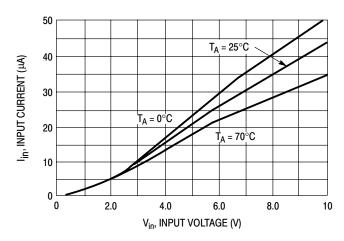


Figure 7. MC3X164–3 Input Current versus Input Voltage

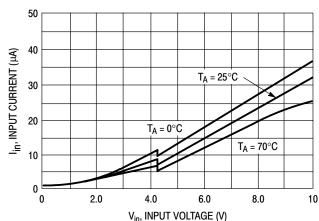


Figure 8. MC3X164-5 Input Current versus Input Voltage

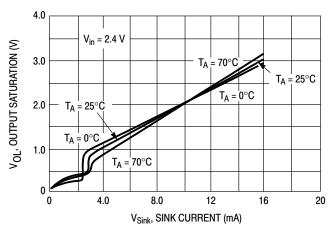


Figure 9. MC3X164-3 Reset Output Saturation versus Sink Current

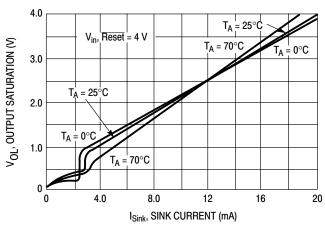


Figure 10. MC3X164–5 Reset Output Saturation versus Sink Current

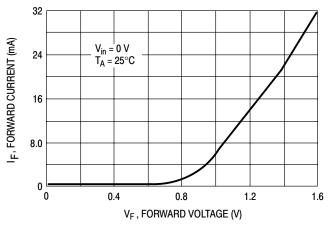


Figure 11. Clamp Diode Forward Current versus Voltage

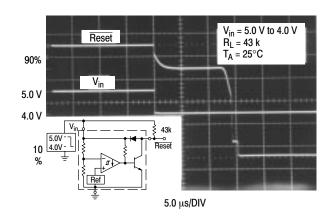
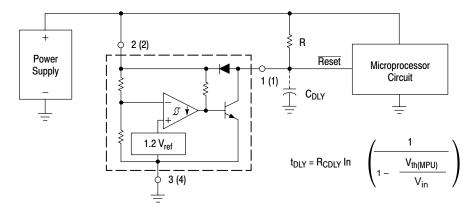
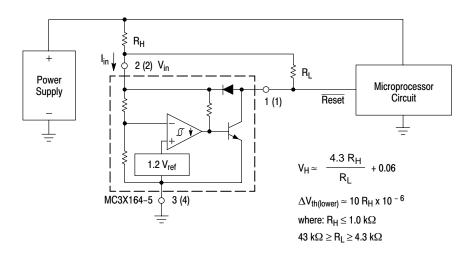


Figure 12. Reset Delay Time (MC3X164–5 Shown)



A time delayed reset can be accomplished with the addition of C_{DLY} . For systems with extremely fast power supply rise times (< 500 ns) it is recommended that the RCDLY time constant be greater than 5.0 μ s. $V_{th(MPU)}$ is the microprocessor reset input threshold.

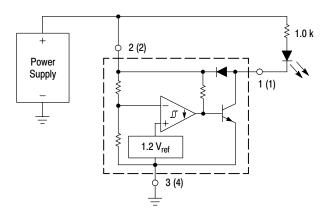
Figure 13. Low Voltage Microprocessor Reset



Test Data					
V _H (mV)	ΔV_{th} (mV)	R _H (Ω)	R_L (k Ω)		
60	0	0	43		
103	1.0	100	10		
123	1.0	100	6.8		
160	1.0	100	4.3		
155	2.2	220	10		
199	2.2	220	6.8		
280	2.2	220	4.3		
262	4.7	470	10		
306	4.7	470	8.2		
357	4.7	470	6.8		
421	4.7	470	5.6		
530	4.7	470	4.3		

Comparator hysteresis can be increased with the addition of resistor R_H . The hysteresis equation has been simplified and does not account for the change of input current l_{in} as V_{in} crosses the comparator threshold (Figure 8). An increase of the lower threshold $\Delta V_{th(lower)}$ will be observed due to l_{in} which is typically 10 μ A at 4.3 V. The equations are accurate to $\pm 10\%$ with R_H less than 1.0 k Ω and R_L between 4.3 k Ω and 43 k Ω .

Figure 14. Low Voltage Microprocessor Reset With Additional Hysteresis (MC3X164–5 Shown)



2 (2)

1 (1)

Solar Cells

3 (4)

Figure 15. Voltage Monitor

Figure 16. Solar Powered Battery Charger

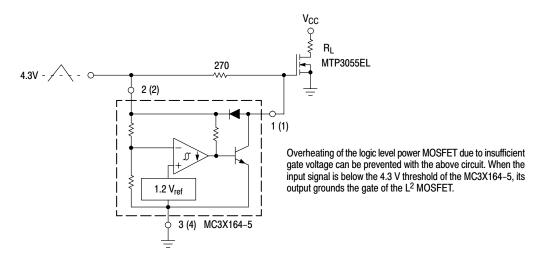


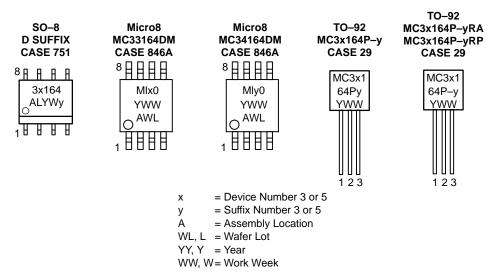
Figure 17. MOSFET Low Voltage Gate Drive Protection Using the MC3X164-5

ORDERING INFORMATION

Device	Package	Shipping
MC33164D-3	SO-8	98 Units / Rail
MC33164D-3R2	SO-8	2500 Units / Tape & Reel
MC33164DM-3R2	Micro8	4000 Units / Tape & Reel
MC33164P-3	TO-92	2000 Units / Box
MC33164P-3RA	TO-92	2000 Units / Tape & Reel
MC33164P-3RP	TO-92	2000 Units / Pack
MC33164D-5	SO-8	98 Units / Rail
MC33164D-5R2	SO-8	2500 Units / Tape & Reel
NCV33164D-5R2*	SO-8	2500 Units / Tape & Reel
MC33164DM-5R2	Micro8	4000 Units / Tape & Reel
MC33164P-5	TO-92	2000 Units / Box
MC33164P-5RA	TO-92	2000 Units / Tape & Reel
MC33164P-5RP	TO-92	2000 Units / Pack
MC34164D-3	SO-8	98 Units / Rail
MC34164D-3R2	SO-8	2500 Units / Tape & Reel
MC34164DM-3R2	Micro8	4000 Units / Tape & Reel
MC334164P-3	TO-92	2000 Units / Box
MC34164P-3RP	TO-92	2000 Units / Pack
MC34164D-5	SO-8	98 Units / Rail
MC34164D-5R2	SO-8	2500 Units / Tape & Reel
MC34164DM-5R2	Micro8	4000 Units / Tape & Reel
MC334164P-5	TO-92	2000 Units / Box
MC34164P-5RA	TO-92	2000 Units / Tape & Reel
MC34164P-5RP	TO-92	2000 Units / Pack

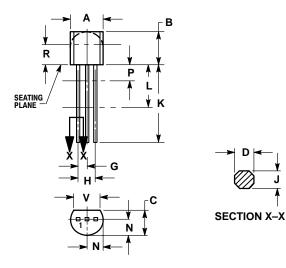
^{*}NCV33164: $T_{low} = -40$ °C, $T_{high} = +125$ °C. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.

MARKING DIAGRAMS



PACKAGE DIMENSIONS

TO-226AA **P SUFFIX** CASE 29-11 **ISSUE AL**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

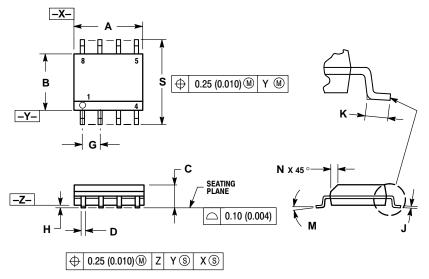
 2. CONTROLLING DIMENSION: INCH.

 3. CONTOUR DO PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.

 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

SO-8 D SUFFIX CASE 751-07 **ISSUE W**



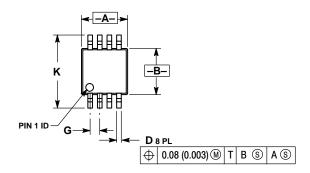
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- SIDE.

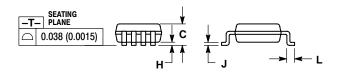
 5. DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	1.27 BSC		0.050 BSC	
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
M	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

PACKAGE DIMENSIONS

Micro8 **DM SUFFIX** CASE 846A-02 ISSUE E





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	2.90	3.10	0.114	0.122
C		1.10		0.043
D	0.25	0.40	0.010	0.016
G	0.65	BSC	0.026	BSC
Н	0.05	0.15	0.002	0.006
J	0.13	0.23	0.005	0.009
K	4.75	5.05	0.187	0.199
L	0.40	0.70	0.016	0.028



Notes

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